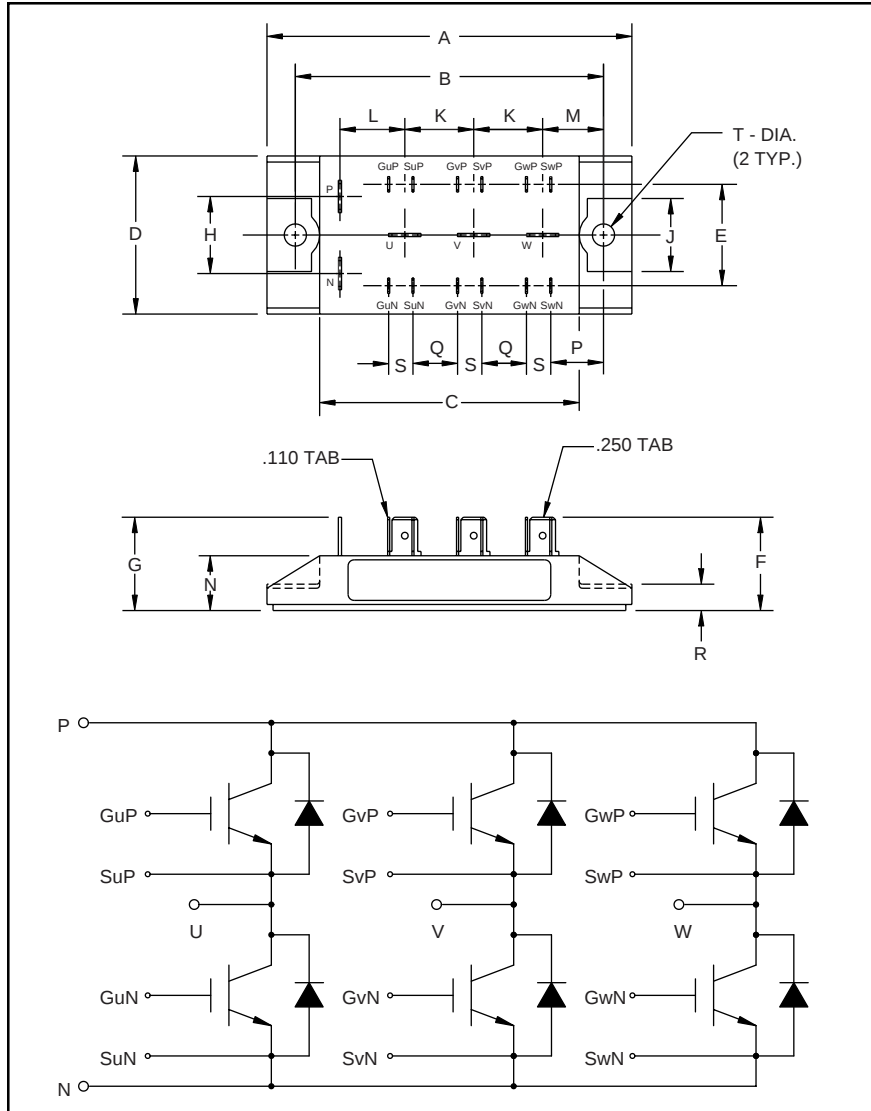


Six-IGBT IGBTMOD™ H-Series Module 15 Amperes/600 Volts



Outline Drawing and Circuit Diagram

Dimensions	Inches	Millimeters
A	3.54	90.0
B	2.99±0.01	76.0±0.2
C	2.52	64.0
D	1.54	39.0
E	0.98	25.0
F	0.90	23.0
G	0.87	22.0
H	0.75	19.0
J	0.71	18.0

Dimensions	Inches	Millimeters
K	0.67	17.0
L	0.63	16.0
M	0.59	15.0
N	0.56	14.1
P	0.51	13.0
Q	0.43	11.0
R	0.26	6.5
S	0.24	6.0
T	0.22 Dia.	Dia. 5.5



Description:

Powerex IGBTMOD™ Modules are designed for use in switching applications. Each module consists of six IGBT Transistors in a three phase bridge configuration, with each transistor having a reverse-connected super-fast recovery free-wheel diode. All components and interconnects are isolated from the heat sinking baseplate, offering simplified system assembly and thermal management.

Features:

- ☐ Low Drive Power
- ☐ Low $V_{CE(sat)}$
- ☐ Discrete Super-Fast Recovery (70ns) Free-Wheel Diode
- ☐ High Frequency Operation (20-25kHz)
- ☐ Isolated Baseplate for Easy Heat Sinking

Applications:

- ☐ AC Motor Control
- ☐ Motion/Servo Control
- ☐ UPS
- ☐ Welding Power Supplies
- ☐ Laser Power Supplies

Ordering Information:

Example: Select the complete part module number you desire from the table below -i.e. CM15TF-12H is a 600V (V_{CES}), 15 Ampere Six-IGBT IGBTMOD™ Power Module.

Type	Current Rating Amperes	V_{CES} Volts (x 50)
CM	15	12

CM15TF-12H

Six-IGBT IGBTMOD™ H-Series Module

15 Amperes/600 Volts

Absolute Maximum Ratings, $T_j = 25^\circ\text{C}$ unless otherwise specified

Ratings	Symbol	CM15TF-12H	Units
Junction Temperature	T_j	-40 to +150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-40 to +125	$^\circ\text{C}$
Collector-Emitter Voltage (G-E SHORT)	V_{CES}	600	Volts
Gate-Emitter Voltage	V_{GES}	± 20	Volts
Collector Current	I_C	15	Amperes
Peak Collector Current	I_{CM}	30*	Amperes
Diode Forward Current	I_F	15	Amperes
Diode Forward Surge Current	I_{FM}	30*	Amperes
Power Dissipation	P_d	100	Watts
Max. Mounting Torque M5 Mounting Screws	—	17	in-lb
Module Weight (Typical)	—	150	Grams
V Isolation	V_{RMS}	2500	Volts

* Pulse width and repetition rate should be such that device junction temperature does not exceed the device rating.

Static Electrical Characteristics, $T_j = 25^\circ\text{C}$ unless otherwise specified

Characteristics	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Collector-Cutoff Current	I_{CES}	$V_{\text{CE}} = V_{\text{CES}}, V_{\text{GE}} = 0\text{V}$	—	—	1.0	mA
Gate Leakage Current	I_{GES}	$V_{\text{GE}} = V_{\text{GES}}, V_{\text{CE}} = 0\text{V}$	—	—	0.5	μA
Gate-Emitter Threshold Voltage	$V_{\text{GE(th)}}$	$I_C = 1.5\text{mA}, V_{\text{CE}} = 10\text{V}$	4.5	6.0	7.5	Volts
Collector-Emitter Saturation Voltage	$V_{\text{CE(sat)}}$	$I_C = 15\text{A}, V_{\text{GE}} = 15\text{V}$	—	2.1	2.8**	Volts
		$I_C = 15\text{A}, V_{\text{GE}} = 15\text{V}, T_j = 150^\circ\text{C}$	—	2.15	—	Volts
Total Gate Charge	Q_G	$V_{\text{CC}} = 300\text{V}, I_C = 15\text{A}, V_{\text{GS}} = 15\text{V}$	—	45	—	nC
Diode Forward Voltage	V_{FM}	$I_E = 15\text{A}, V_{\text{GS}} = 0\text{V}$	—	—	2.8	Volts

** Pulse width and repetition rate should be such that device junction temperature rise is negligible.

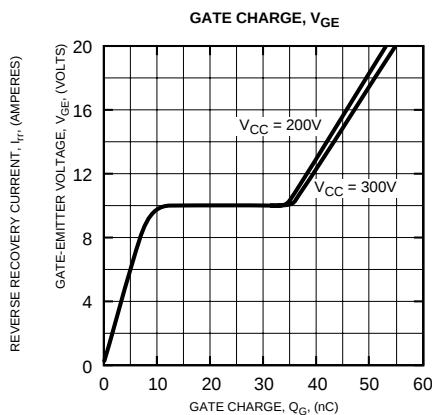
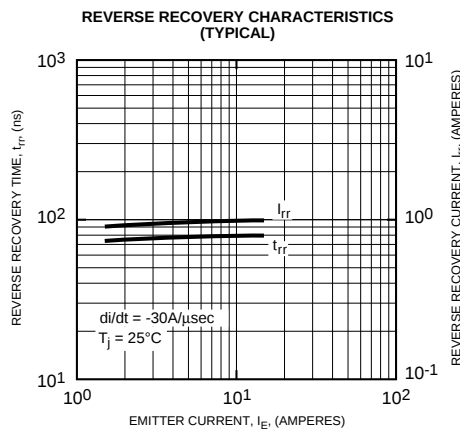
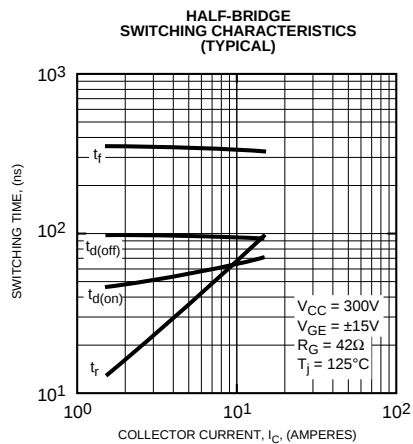
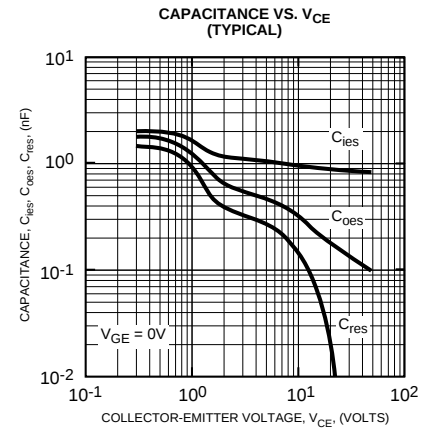
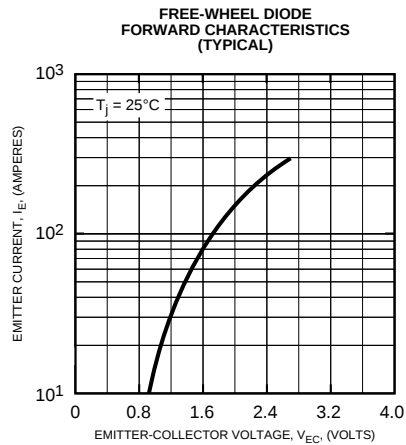
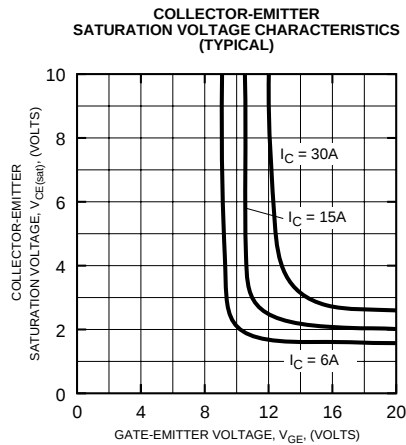
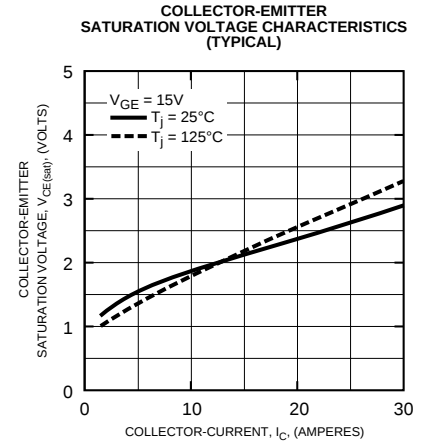
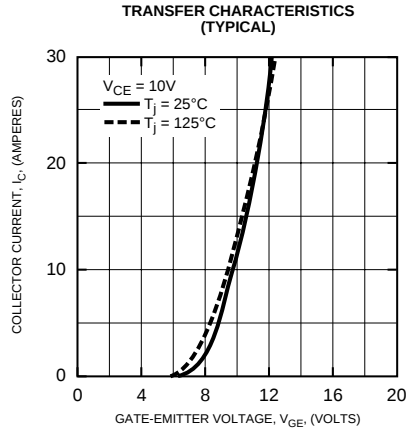
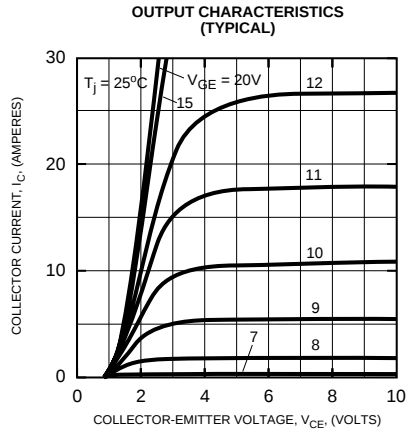
Dynamic Electrical Characteristics, $T_j = 25^\circ\text{C}$ unless otherwise specified

Characteristics	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Input Capacitance	C_{ies}		—	—	1.5	nF
Output Capacitance	C_{oes}	$V_{\text{GE}} = 0\text{V}, V_{\text{CE}} = 10\text{V}, f = 1\text{MHz}$	—	—	0.5	nF
Reverse Transfer Capacitance	C_{res}		—	—	0.3	nF
Resistive	Turn-on Delay Time	$V_{\text{CC}} = 300\text{V}, I_C = 15\text{A}, V_{\text{GE1}} = V_{\text{GE2}} = 15\text{V}, R_G = 42\Omega$	—	—	120	ns
Load	Rise Time		—	—	300	ns
Switch	Turn-off Delay Time		—	—	200	ns
Times	Fall Time		—	—	300	ns
Diode Reverse Recovery Time	t_{rr}	$I_E = 15\text{A}, di_E/dt = -30\text{A}/\mu\text{s}$	—	—	110	ns
Diode Reverse Recovery Charge	Q_{rr}	$I_E = 15\text{A}, di_E/dt = -30\text{A}/\mu\text{s}$	—	0.04	—	μC

Thermal and Mechanical Characteristics, $T_j = 25^\circ\text{C}$ unless otherwise specified

Characteristics	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Thermal Resistance, Junction to Case	$R_{\text{th(j-c)}}$	Per IGBT	—	—	1.30	$^\circ\text{C}/\text{W}$
Thermal Resistance, Junction to Case	$R_{\text{th(j-c)}}$	Per FWDi	—	—	3.50	$^\circ\text{C}/\text{W}$
Contact Thermal Resistance	$R_{\text{th(c-f)}}$	Per Module, Thermal Grease Applied	—	—	0.092	$^\circ\text{C}/\text{W}$

CM15TF-12H
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